

2N2222 (NPN Transistor)



Pin Configuration:

1. Emitter
2. Base
3. Collector

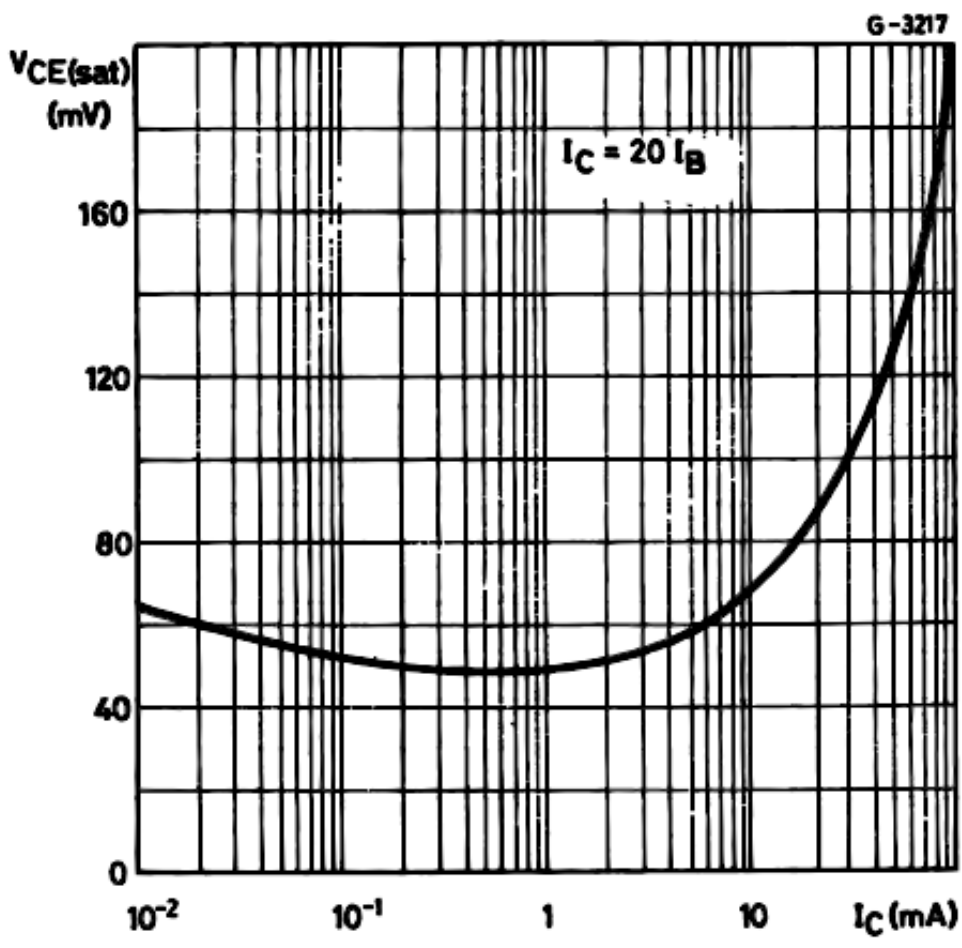
Description	Symbol	Test Condition	Value		Unit
			Minimum	Maximum	
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = 10\text{mA}, I_B = 0$	30	-	V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	60	-	
Emitter Base Breakdown Voltage	V_{EB0}	$I_E = 10\mu\text{A}, I_C = 0$	5	-	
Collector Leakage Current	I_{CBO}	$V_{CB} = 50\text{V}, I_E = 0$	-	10	nA
		$V_{CB} = 50\text{V}, I_E = 0$ $T_a = 150^\circ\text{C}$		10	μA
Collector Emitter Saturation Voltage	$*V_{CE(Sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$	-	0.4 1.6	V
Base Emitter Saturation Voltage	$*V_{BE(Sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$	0.6	1.3 2.6	

[Datasheet](#)

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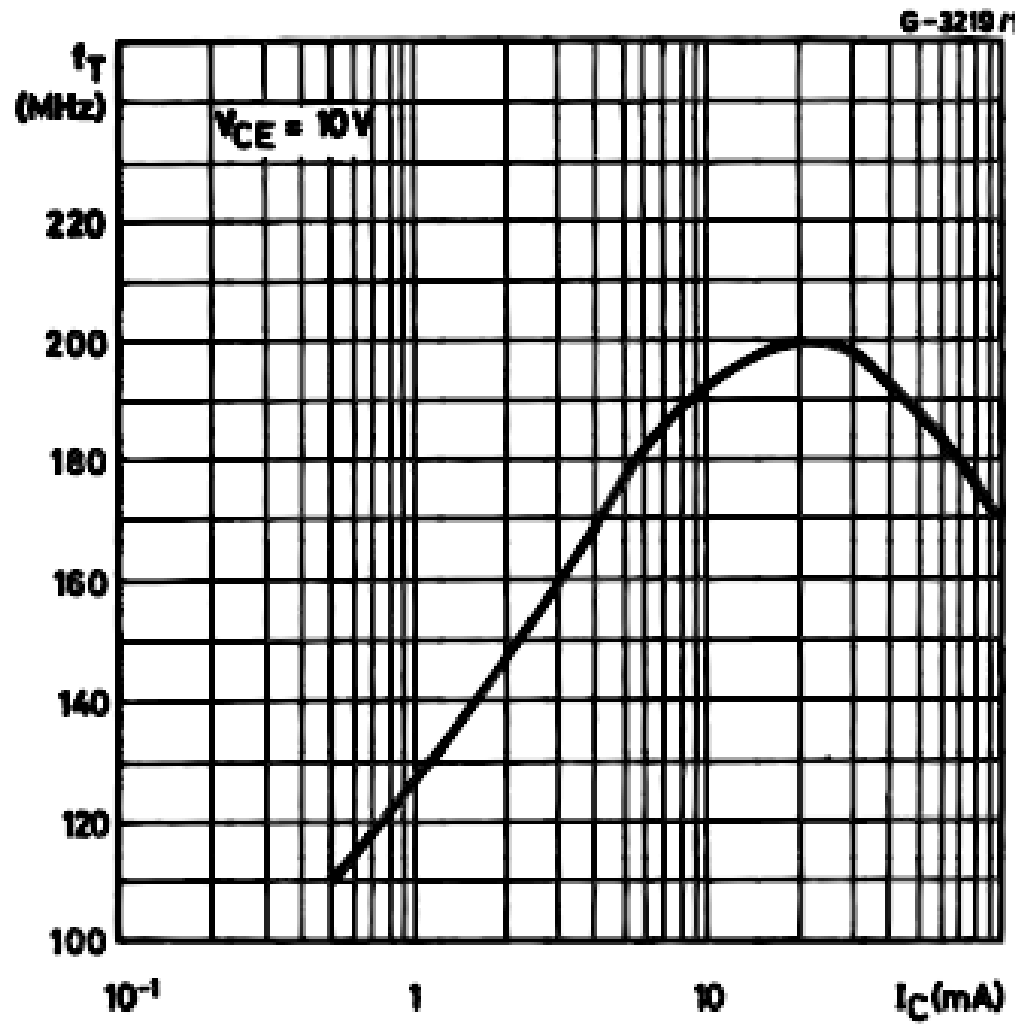
Parameter	Symbol	Test Condition	2N2222		Unit
			Minimum	Maximum	
DC Current Gain	h_{FE}	$I_C = 0.1\text{mA}, V_{CE} = 10\text{V}^*$	35	300	-
		$I_C = 1\text{mA}, V_{CE} = 10\text{V}$	50		
		$I_C = 10\text{mA}, V_{CE} = 10\text{V}^*$	75		
		$I_C = 150\text{mA}, V_{CE} = 1\text{V}^*$	50		
		$I_C = 150\text{mA}, V_{CE} = 1\text{V}^*$	100		
		$I_C = 500\text{mA}, V_{CE} = 10\text{V}^*$	30		
Dynamic Characteristics					
Transition Frequency	f_t	$I_C = 20\text{mA}, V_{CE} = 20\text{V}$ $f = 100\text{MHz}$	250	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0$ $f = 100\text{kHz}$	-	8	pF
Input Capacitance	C_{ib}	$V_{EB} = 0.5\text{V}, I_C = 0$ $f = 100\text{kHz}$	-	30	
Switching Characteristics					
Delay Time	t_d	$I_C = 150\text{mA}, I_{B1} = 15\text{mA}$	-	10	ns
Rise Time	t_r	$V_{CC} = 30\text{V}, V_{BE(\text{off})} = 0.5\text{V}$	-	25	
Storage Time	t_s	$I_C = 150\text{mA}, I_{B1} = 15\text{mA}$	-	225	
Fall Time	t_f	$I_{B2} = 15\text{mA}, V_{CC} = 30\text{V}$	-	60	

BC107 (NPN Transistor)



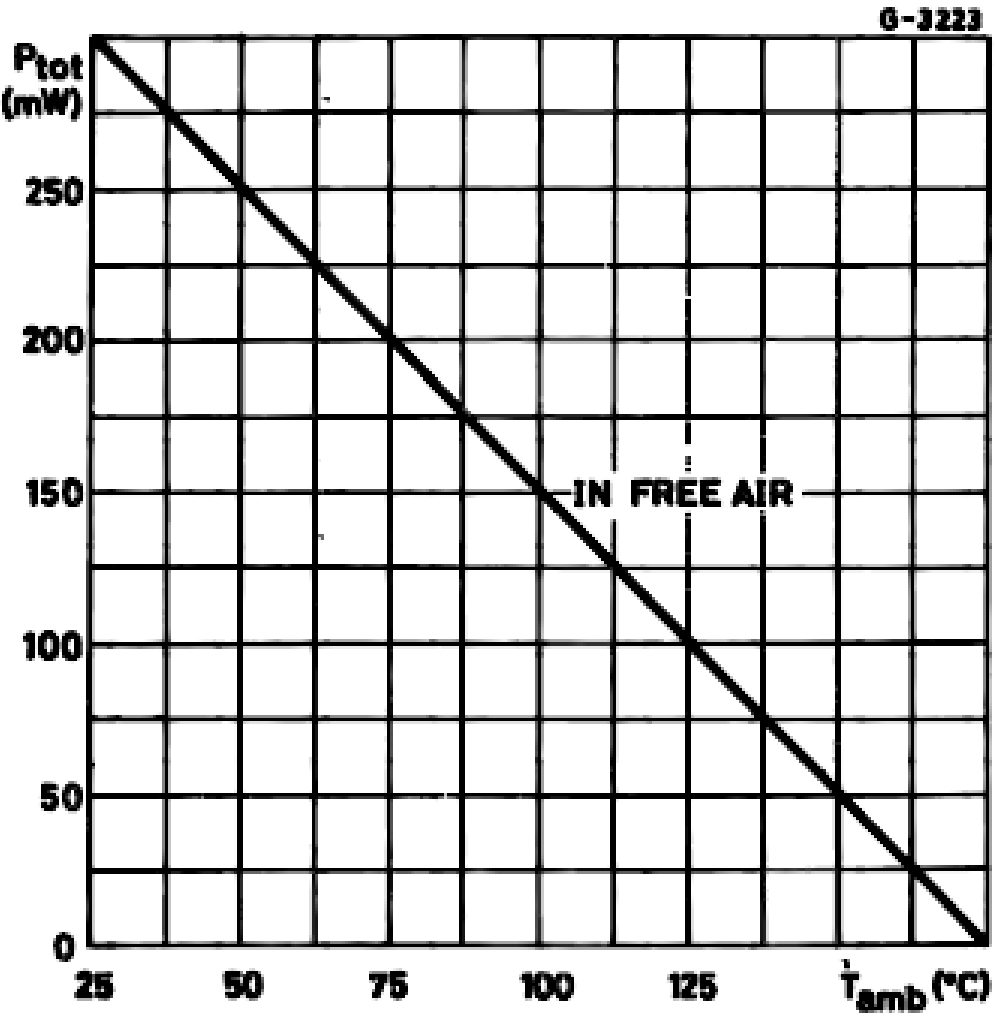
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BC107 (NPN Transistor)



f_T : Transient Frequency

BC107 (NPN Transistor)



Power Rating Chart

BC177 (PNP Transistor)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	-50	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-45	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-100	mA
I_{CM}	Collector Peak Current	-200	mA
P_{tot}	Total Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$	0.3	W
T_{stg}	Storage Temperature	-65 to 175	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

[Datasheet](#)